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				Application Number	10/582,392
				Filing Date	June 28, 2007
				First Named Inventor	Horsky et al.
				Group Art Unit	2821
				Examiner Name	Bernard Souw
Sheet	1	of	1	Attorney Docket Number	211843-00044

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	5,497,006	03-05-1996	Sferlazzo	
	A2	2008-0121811	05-29-2008	Horsky	
	A3	2004-0002202	01-01-2004	Horsky	
	A4	2008-0223409	04-18-2008	Horsky	
	A5	12/234,202	09-19-2008	Horsky	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ –Number ⁴ – Kind Code ⁵ (if known)				
	B1	WO 2005/059942 A2				
	B2	WO 2004/003973 A3				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher city and/or country where published	T ²
	C1	E.J. Collart et al. "Co-Implantation with Conventional Spike Anneal Solutions for 45 nm Ultra-Shallow Junction Formation", Proceedings of the Eight International Workshop on: Fabrication, Characterization and Modeling Of Ultra-Shallow Doping Profiles in Semiconductors, June 2005, p. 327	
	C2	S. Birk et al. "Modeling the Suppression of Boron Diffusion in Si/SiO₂ Due to Carbon Incorporation", <i>ibid.</i>, p. 315	
	C3	L. S. Robertson et al., "The Effect of Impurities and Activation of Ion Implanted boron in Silicon", Mat. Res. Soc. Symp. Vol. 610, pp. B5.8.1-B5.8.6 (2000)	
	C4	Mara F. Law et al., "Influence of Carbon on the diffusion of Interstitials and Boron in Silicon", <i>ibid.</i>, pp. B7.4.1-B7.4.5	
	C5	P. A. Stolk et al., "Understanding and Controlling Transient Enhanced Dopant Diffusion in Silicon", Mat. Res. Soc. Symp. Proc. Vol. 354, pp. 307-318 (1995)	
	C6	M. Ueda et al., "High Dose Nitrogen and Carbon Shallow Implantation in Si by Plasma Immersion Ion Implantation", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) pp. 715-720;	
	C7	Jorg K. N. Lindner et al., "Ion Beam Synthesis of Buried SiC Layers in Silicon: Basic Physical Processes", Nuclear Instruments and Methods Research B 178 (2001) pp. 44-54	
	C8	K. N. Lindner et al., "Mechanisms of SiC Formation in the Ion Beam Synthesis of 3 C--SiC Layers in Silicon", Materials Science Forum Vols. 264-268 (1998) pp. 215-218	
	C9	Kah-Wee An et al., "Thin body Silicon-on-insulator N-MOSFET with Silicon-Carbon Source/Drain Regions for Performance Enhancement", IEDM Workshop, Washington, D.C., December, 2005	
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Examiner Signature		/Bernard Souw/	05/26/2010

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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